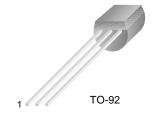


## **PN3643**

### **NPN General Purpose Amplifier**

• This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300mA.



1. Emitter 2. Base 3. Collector

### **Absolute Maximum Ratings\*** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
   These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

### **Electrical Characteristics** $T_A$ =25°C unless otherwise noted

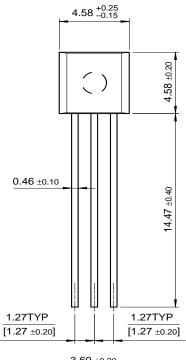
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Chara	cteristics		•		•
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage *	$I_C = 10 \text{mA}, I_B = 0$	30		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	60		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5.0		V
I <sub>CES</sub>	Collector Cut-off Current	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0 V <sub>CB</sub> = 50V, I <sub>E</sub> = 0, T <sub>A</sub> = 65°C		50 1.0	nA μA
On Chara	cteristics	•			
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = 10V, I <sub>C</sub> = 150mA V <sub>CE</sub> = 10V, I <sub>C</sub> = 500mA	100 20	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA		0.22	V
Small Sign	nal Characteristics		•	•	
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, f = 140KHz		8.0	pF
η	Collector Efficientcy	$V_{CE} = 15V, f = 30MHz$ $R_{G} = 140\Omega, R_{L} = 260\Omega$	60		%
G <sub>pe</sub>	Amplifier Power Gain	$V_{CE} = 15V, f = 30MHz$ $R_{G} = 140\Omega, R_{L} = 260\Omega$	10		dB
h <sub>fe</sub>	Small Signal Current Gain	$I_C = 50$ mA, $V_{CE} = 5.0$ V, $f = 100$ MHz	2.5		

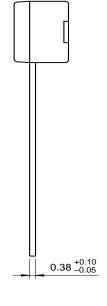
\* Pulse Test: Pulse Width ≤ 300ms, Duty Cycle ≤ 2.0%

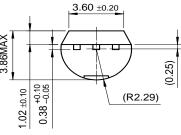
Thermal Characteristics T <sub>A</sub> =25°C unless otherwise noted				
Symbol	Parameter	Max.	Units	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case 83.3 °C/		°C/W	
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient 200 °C		°C/W	

# **Package Dimensions**

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EnSigna™	I <sup>2</sup> C <sup>TM</sup>	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
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